

Transmissive Optical Sensor

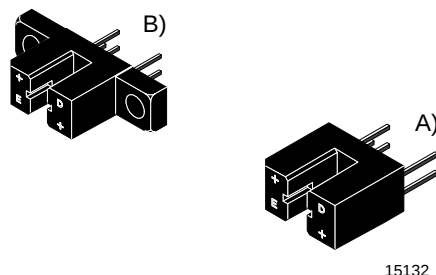
Description

This device has a compact construction where the emitting-light sources and the detectors are located face to face on the same optical axes.

The operating wavelength is 950 nm. The detector consists of a photologic-IC with Schmitt trigger and open collector output.

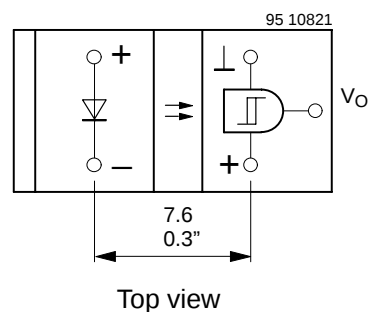
Applications

- Detection of opaque material, documents etc.
- Paper position sensor in copy machines
- Position sensor for shaft encoder



Features

- Output: 'LOW' when infrared beam is not interrupted
- Inverter-open collector
- TTL compatible
- Built-in voltage regulator
- Plastic polycarbonate case, protected against ambient light
- No adjustment necessary
- Two package variations



Handling Precautions

Connect a capacitor C of more than 100 nF between V_{S1} and ground in order to stabilize power supply voltage!

Order Instruction

Ordering Code	Resolution (mm) / Aperture (mm)	Remarks
TCSS1100 ^{A)}	0.6 / 1.0	No mounting flags
TCSS2100 ^{B)}	0.6 / 1.0	With two mounting flags

Absolute Maximum Ratings

Input (Emitter)

Parameter	Test Conditions	Symbol	Value	Unit
Reverse voltage		V_R	6	V
Forward current		I_F	60	mA
Forward surge current	$t_p \leq 10 \mu s$	I_{FSM}	3	A
Power dissipation	$T_{amb} \leq 25^\circ C$	P_V	100	mW
Junction temperature		T_j	100	$^\circ C$

Output (Detector)

Parameter	Test Conditions	Symbol	Value	Unit
Supply voltages		V_{S1}	6.5	V
		V_{S2}	18	V
Output current		I_O	20	mA
Power dissipation	$T_{amb} \leq 25^\circ C$	P_V	250	mW
Junction temperature		T_j	100	$^\circ C$

Coupler

Parameter	Test Conditions	Symbol	Value	Unit
Total power dissipation	$T_{amb} \leq 25^\circ C$	P_{tot}	250	mW
Ambient temperature range		T_{amb}	-25 to +85	$^\circ C$
Storage temperature range		T_{stg}	-40 to +100	$^\circ C$
Soldering temperature	2 mm from case, $t \leq 5 s$	T_{sd}	260	$^\circ C$

Electrical Characteristics ($T_{amb} = 25^\circ C$)

Input (Emitter)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Forward voltage	$I_F = 50 \text{ mA}$	V_F		1.25	1.6	V
Junction capacitance	$V_R = 0, f = 1 \text{ MHz}$	C_j		50		pF

Output (Detector)

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Supply voltage range		V_{S1}	4.75		5.25	V
		V_{S2}	4.0		16	V

Coupler

Parameter	Test Conditions	Symbol	Min.	Typ.	Max.	Unit
Supply current	$V_{S1} = 16 \text{ V}$	I_{S1}		3	5	mA
Output current	$V_{S1} = V_{S2} = 16 \text{ V}, I_F = 0$	I_{OH}			1	μA
Input threshold current	$V_{S1} = 5 \text{ V}$	I_{FT}		5	10	mA
Hysteresis	$V_{S1} = 5 \text{ V}$	I_{Foff}/I_{Fon}		80		%
Output voltage	$I_{OL} = 16 \text{ mA}, I_F \geq I_{TF}, V_{S1} = 5 \text{ V}$	V_{OL}		0.15	0.4	V
Switching frequency	$I_F = 3 \times I_{FT}, V_{S1} = V_{S2} = 5 \text{ V}, R_L = 1 \text{ k}\Omega$	f_{sw}		200		kHz

Switching Characteristics

Parameter	Test Conditions	Symbol	Typ.	Unit
Rise time	$V_{S1} = V_{S2} = 5\text{ V}$, $I_F = 3 \times I_{FT}$, $R_L = 1\text{ k}\Omega$ (see figure 1)	t_r	50.0	ns
Turn-on time		t_{on}	1.0	μs
Fall time		t_f	20.0	ns
Turn-off time		t_{off}	3.0	μs

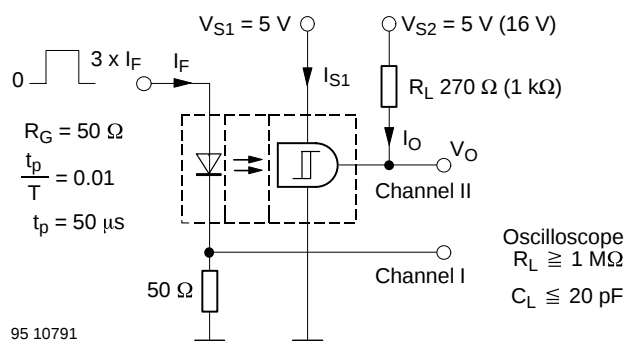


Figure 1. Test circuit for: t_r , t_{on} , t_f , t_{off}

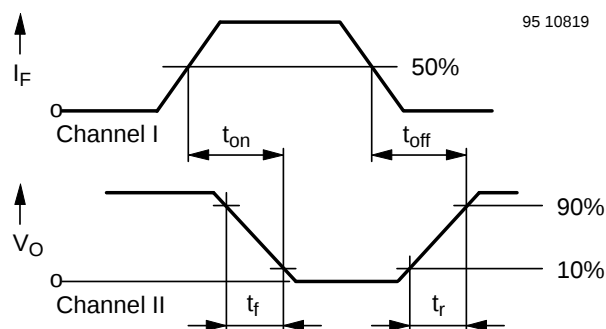


Figure 2. Pulse diagram

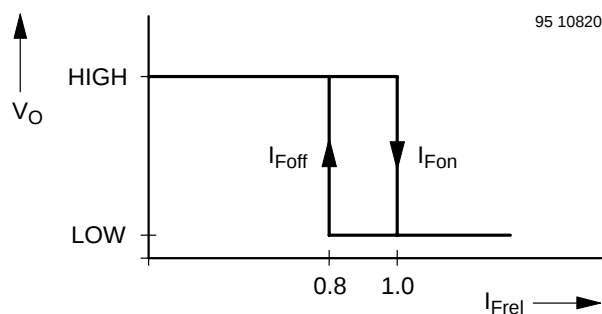


Figure 3. Hysteresis

Typical Characteristics ($T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified)

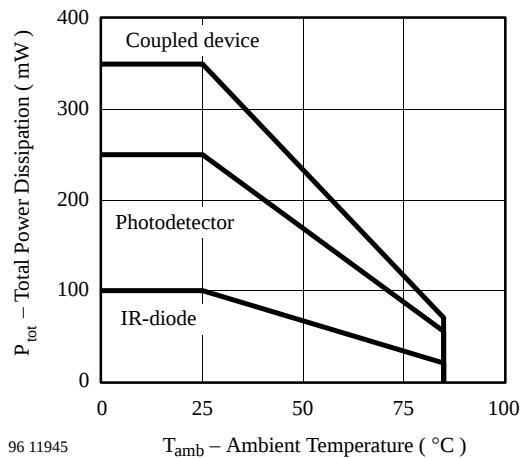


Figure 4. Total Power Dissipation vs. Ambient Temperature

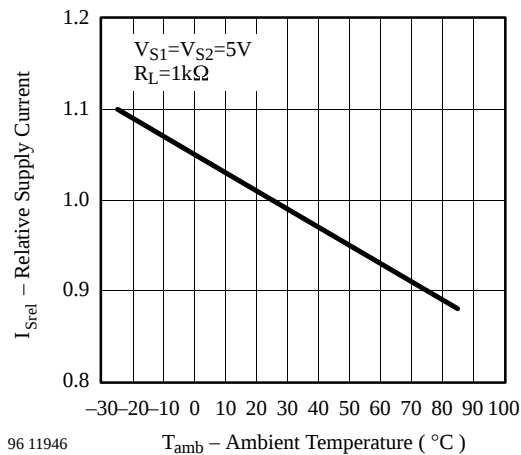


Figure 7. Relative Supply Current vs. Ambient Temperature

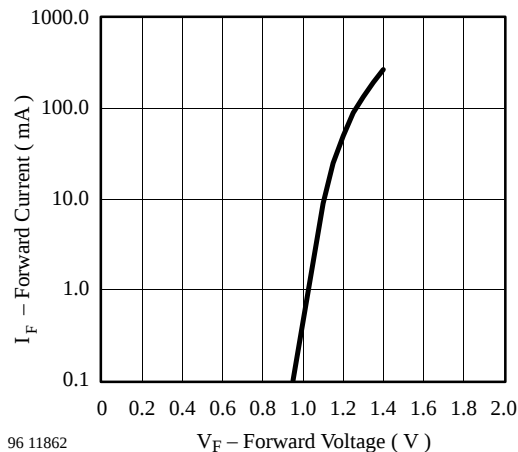


Figure 5. Forward Current vs. Forward Voltage

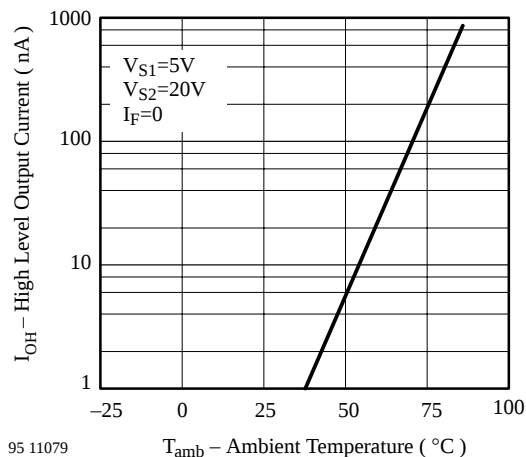


Figure 8. High Level Output Current vs. Ambient Temperature

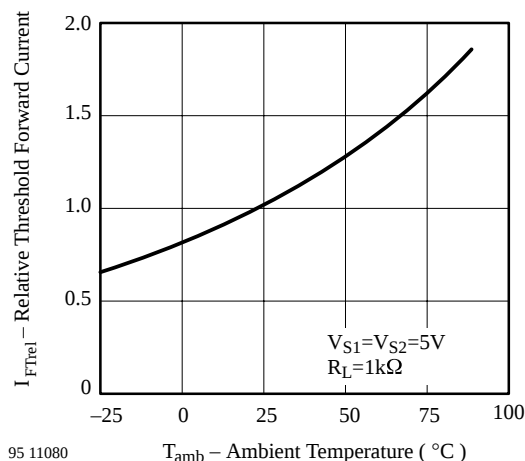
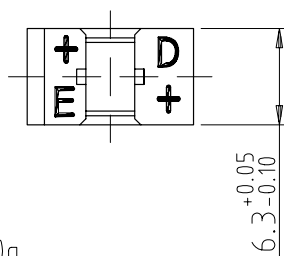
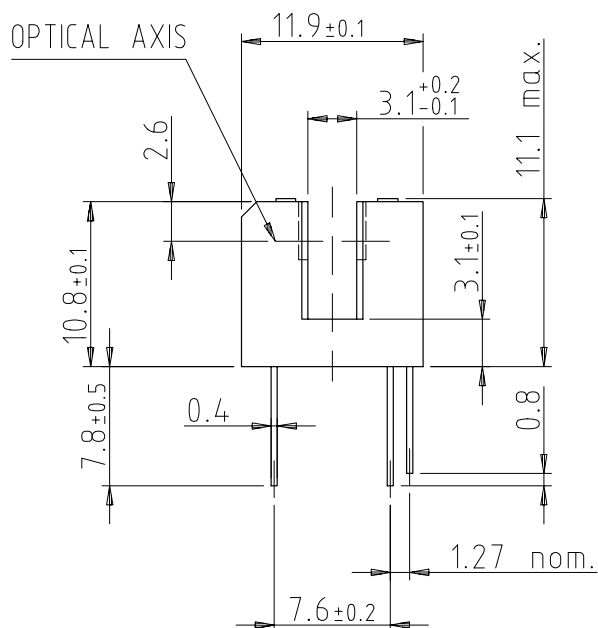


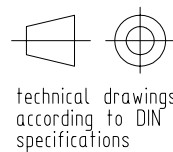
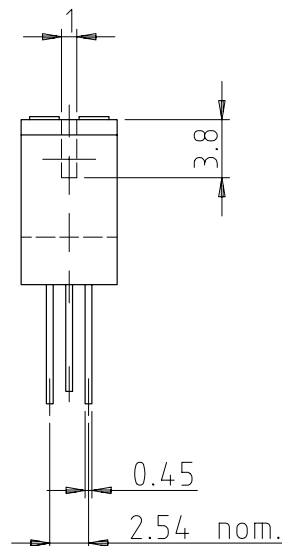
Figure 6. Relative Threshold Forward Current vs. Ambient Temperature



Dimensions of TCSS1100 in mm

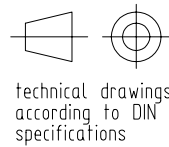
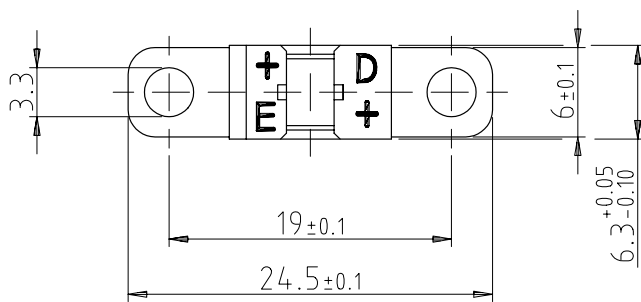
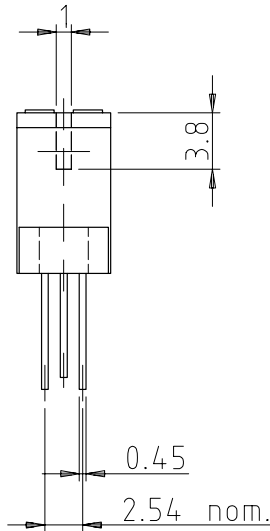
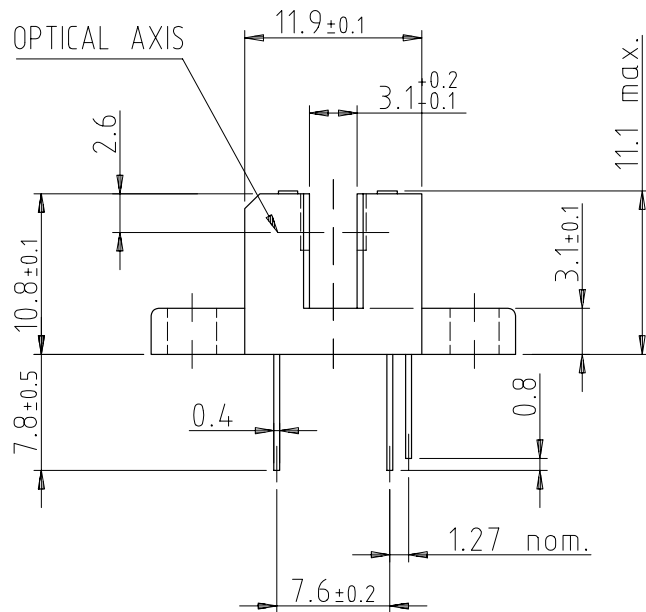


weight: ca. 0.80g



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Dimensions of TCSS2100 in mm



weight: ca. 0.90g

96 12097



Ozone Depleting Substances Policy Statement

It is the policy of **Vishay Semiconductor GmbH** to

1. Meet all present and future national and international statutory requirements.
2. Regularly and continuously improve the performance of our products, processes, distribution and operating systems with respect to their impact on the health and safety of our employees and the public, as well as their impact on the environment.

It is particular concern to control or eliminate releases of those substances into the atmosphere which are known as ozone depleting substances (ODSs).

The Montreal Protocol (1987) and its London Amendments (1990) intend to severely restrict the use of ODSs and forbid their use within the next ten years. Various national and international initiatives are pressing for an earlier ban on these substances.

Vishay Semiconductor GmbH has been able to use its policy of continuous improvements to eliminate the use of ODSs listed in the following documents.

1. Annex A, B and list of transitional substances of the Montreal Protocol and the London Amendments respectively
2. Class I and II ozone depleting substances in the Clean Air Act Amendments of 1990 by the Environmental Protection Agency (EPA) in the USA
3. Council Decision 88/540/EEC and 91/690/EEC Annex A, B and C (transitional substances) respectively.

Vishay Semiconductor GmbH can certify that our semiconductors are not manufactured with ozone depleting substances and do not contain such substances.

We reserve the right to make changes to improve technical design and may do so without further notice.

Parameters can vary in different applications. All operating parameters must be validated for each customer application by the customer. Should the buyer use Vishay Telefunken products for any unintended or unauthorized application, the buyer shall indemnify Vishay Telefunken against all claims, costs, damages, and expenses, arising out of, directly or indirectly, any claim of personal damage, injury or death associated with such unintended or unauthorized use.

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Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

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